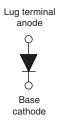


High Performance Schottky Rectifier, 120 A





HALF-PAK (D-67)

PRIMARY CHARACTERISTICS			
I _{F(AV)}	120 A		
V_{R}	100 V		
Package	HALF-PAK (D-67)		
Circuit configuration	Single diode		

FEATURES

- 175 °C T_J operation
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Designed and qualified for industrial level
- UL approved file E222165
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

The VS-123NQ.. high current Schottky rectifier module series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in high current switching power supplies, plating power supplies, UPS systems, converters, freewheeling diodes, welding, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS	CHARACTERISTICS VALUES			
I _{F(AV)}	Rectangular waveform	120	А		
V _{RRM}		100	V		
I _{FSM}	t _p = 5 μs sine	12 800	А		
V _F	120 A _{pk} , T _J = 125 °C	0.73	V		
T _J	Range	-55 to +175	°C		

VOLTAGE RATINGS			
PARAMETER	SYMBOL	VS-123NQ100PbF	UNITS
Maximum DC reverse voltage	V_{R}	100	
Maximum working peak reverse voltage	V_{RWM}	100	

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current See fig. 5	I _{F(AV)}	50 % duty cycle at T _C = 133 °C, rectangular waveform		120	А
Maximum peak one cycle non-repetitive surge current		5 µs sine or 3 µs rect. pulse	Following any rated load condition and with	12 800	Α
See fig. 7	IFSM	10 ms sine or 6 ms rect. pulse	rated V _{RRM} applied	1800	
Non-repetitive avalanche energy	E _{AS}	T _J = 25 °C, I _{AS} = 5.5 A, L = 1 mH		15	mJ
Repetitive avalanche current	I _{AR}	Current decaying linearly to zero in 1 μ s Frequency limited by T _J maximum V _A = 1.5 x V _R typical		1	А



ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CO	VALUES	UNITS	
Maximum forward voltage drop), (1)	120 A	T _J = 25 °C	0.91	V
		240 A		1.26	
See fig. 1	V _{FM} ⁽¹⁾	120 A	- T _J = 125 °C	0.73	
		240 A		0.9	
Maximum reverse leakage current	I _{RM}	T _J = 25 °C	V _R = Rated V _R	3	mA
See fig. 2		T _J = 125 °C	v _R = nateu v _R	40	IIIA
Maximum junction capacitance	C _T	V _R = 5 V _{DC} (test signal range 100 kHz to 1 MHz) 25 °C		2650	pF
Typical series inductance	L _S	From top of terminal hole to mounting plane		7.0	nH
Maximum voltage rate of change	dV/dt	Rated V _R		10 000	V/µs

Note

⁽¹⁾ Pulse width = $500 \mu s$

THERMAL - MECHA	THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and stora	age temperature range	T _J , T _{Stg}		-55 to +175	°C	
Maximum thermal resistance, junction to case		R _{thJC}	DC operation See fig. 4	0.38	°C/W	
Typical thermal resistance,	case to heatsink	R _{thCS}	Mounting surface, smooth and greased	0.05	0.05	
Approximate weight				30	g	
				1.06	OZ.	
Mounting torque -	minimum		Non-lubricated threads 4 (35.4) 3.4 (30)	3 (26.5)		
	maximum			4 (35.4)	N · m (lbf · in)	
Terminal torque	minimum			3.4 (30)		
	maximum			5 (44.2)		
Case style				HALF-PAK module		

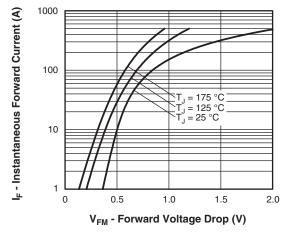


Fig. 1 - Maximum Forward Voltage Drop Characteristics

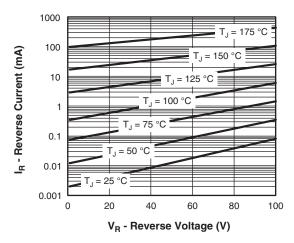


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



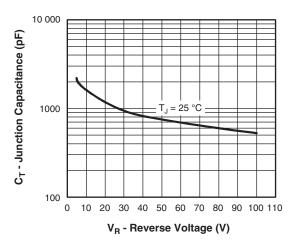


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

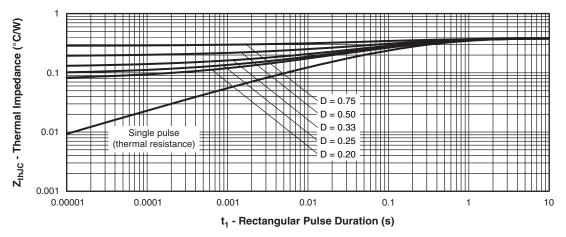


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

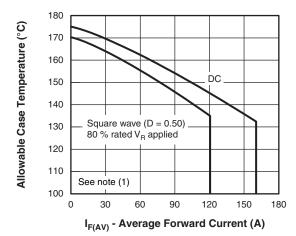


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

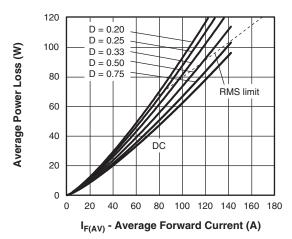


Fig. 6 - Forward Power Loss Characteristics

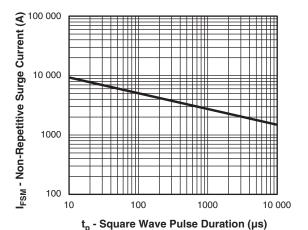


Fig. 7 - Maximum Non-Repetitive Surge Current

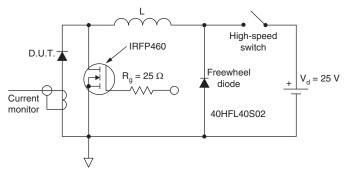


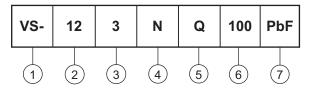
Fig. 8 - Unclamped Inductive Test Circuit

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = rated V_R

ORDERING INFORMATION TABLE

Device code



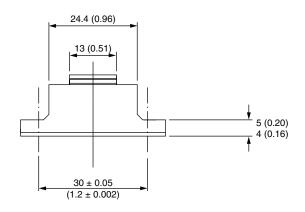
- Vishay Semiconductors product
- Average current rating (x 10)
- Product silicon identification
- N = not isolated
- Q = Schottky rectifier diode
- Voltage rating (100 = 100 V)
- Lead (Pb)-free

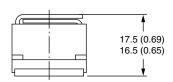
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95020		

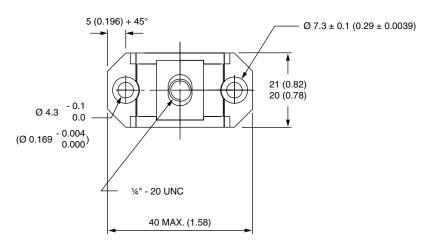


D-67 HALF-PAK

DIMENSIONS in millimeters (inches)









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SK34B-TP SS3003CH-TL-E GA01SHT18 CRS10I30A(TE85L,QM MA4E2501L-1290 MBRB30H30CT-1G SB007-03C-TB-E SK32A-TP
SK33B-TP SK35A-TP SK38B-TP NRVBM120LT1G NTE505 NTSB30U100CT-1G SS15E-TP VS-6CWQ10FNHM3 ACDBA1100LR-HF
ACDBA1200-HF ACDBA140-HF ACDBA2100-HF ACDBA3100-HF CDBQC0530L-HF CDBQC0240LR-HF ACDBA340-HF
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